B.E. ELECTRONICS AND TELE-COMMUNICATION ENGINEERING EXAM 2019 (OLD)

FIRST YEAR FIRST SEMESTER PHYSICAL ELECTRONICS

Time: 3 hours

(All parts of the same question must be answered together) Full Marks: 100

Answer Question no. 1 and any SEVEN from the rest.

| 1. | Explain (any SIX): | 6x. |
|-----------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------|
| | a) Compound semiconductor | UA. |
| | b) Unit cell | |
| | c) Cubic lattice | |
| | d) Free electron theory of metals | |
| | e) Carrier effective mass | |
| | f) Einstein relation | |
| | g) Life time of minority carriers | |
| - | h) Ionized impurity scattering. | |
| 2.a) | Determine the variation of potential energy of an electron with distance along a one- dimensional mono-atomic crystal and construct the corresponding Kronig-Penney model. | . 3+2 |
| [°] b) | State and explain Bloch Theorem. | 5 |
| 3. | Construct the general time-dependent Schrödinger equation with the help of relevant quantum mechanical operators. Derive its time-independent form. | 5+5 |
| 4. | Determine the wave function for an electron confined in an infinitely deep potential well. | 10 |
| 5. | Establish the energy dependence of density-of-states function $D(E)$ for electrons in the conduction band of a semiconductor system, assuming the $E-k$ relation to be parabolic. Also sketch variation of $D(E)$ with E . | 8+2 |
| 6. | Derive an expression for concentration of electrons in the conduction band of an non-degenerate semiconductor. | 10 |
| 7. | Describe how you can obtain an <i>n</i> -type semiconductor from an intrinsic one. Also express location of the Fermi level in terms of electron concentrations in the above two semiconductors. | 6+4 |

What is phonon? Compare the features of Acoustic phonon and Optic phonon. 8. 2+8 Formulate the continuity equation for excess electrons in a p-type semiconductor, and 9. 7+3 modify it under steady state minority carrier injection. Describe Hall experiment and the scheme for determining majority carrier 10. 10 concentration and conductivity type of the given semiconductor sample. Write note on (any ONE): 11. 1x10 a)Recombination of carriers, b) Temperature dependence of Carrier concentration in extrinsic semiconductor, c) Experimental determination of Carrier effective mass.